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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
Sheet	1	of	1	Application Number	10/091,338
				Filing Date	March 6, 2002
				First Named Inventor	Toru MITSUKI et al.
				Group Art Unit	2824
				Examiner Name	Bradley Smith
				Attorney Docket Number	0756-2448

U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No.	U.S. Patent Document		Name of Patent or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Paragraph or Relevant Figure Appear
		Number	Kind Code (if known)			

FOREIGN PATENT DOCUMENTS								
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		Other	Number	Kind Code (if known)				
TSKS		JP	07-162004			06/23/1995		AB
		WO	93-10555			05/27/1993		AB
		JP	04-035021			02/05/1992		AB
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			1*
TSKS		H. Koseki et al., Recent Progress of Low Temperature Poly-Si Technology, Electronic Display Forum, Pages 4-31 to 4-38 and English Translation, Pages 1-21, April 15, 1999.			14
TSKS		Kenji Sera et al., Uniformity Improvement of Excimer Laser Crystallized Poly-Si Thin Film Transistors, AM-LCD '96/IDM '96, Pages 85-88.			
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TSKS		M. Fuse et al., Performance of Poly-Si Thin Film Transistors Fabricated by Excimer-Laser Annealing of SiH ₄ and Si ₂ H ₆ Source Low Pressure Vapor Deposited α-Si Films With or Without Solid-Phase Crystallization, Solid State Phenomena, Vols. 37-38, Pages 565-570, 1994.			

Examiner Signature	TSKS	Date Considered	6/15/04
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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